

Description

The SXG120N12T uses advanced **SGT II** technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 120V$ $I_D = 120A$

$R_{DS(ON)} < 6.8m\Omega$ @ $V_{GS}=10V$

Application

Mobile phone fast charging

Brushless motor

Home appliance control board

**Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)**

Symbol	Parameter	Value	Units
V_{DSS}	Drain-to-Source Voltage	120	V
$I_D @ T_A=25^\circ C$	Continuous Drain Current ¹	120	A
$I_D @ T_A=100^\circ C$	Continuous Drain Current ¹	60	A
IDM^{a1}	Pulsed Drain Current	320	A
EAS _{a2}	Single pulse avalanche energy	240	mJ
IAR	Single pulse avalanche current	40	A
V_{GS}	Gate-to-Source Voltage	± 20	V
P_D	Power Dissipation	125	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150	°C
T_L	Maximum Temperature for Soldering	300	°C
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	50	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
VDSS	Drain to Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	120	135	--	V
IDSS	Drain to Source Leakage Current	$V_{DS} = 120\text{V}, V_{GS}=0\text{V}$	--	--	1	μA
IGSS(F)	Gate to Source Forward Leakage	$V_{GS} = +20\text{V}$	--	--	100	nA
IGSS(R)	Gate to Source Reverse Leakage	$V_{GS} = -20\text{V}$	--	--	-100	nA
VGS(TH)	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D = 250\mu\text{A}$	1.2	1.8	3.0	V
RDS(ON)1	Drain-to-Source On-Resistance	$V_{GS}=10\text{V}, I_D=20\text{A}$	--	6.0	6.8	$\text{m}\Omega$
RDS(ON)1	Drain-to-Source On-Resistance	$V_{GS}=4.5\text{V}, I_D=10\text{A}$	--	8.5	10	$\text{m}\Omega$
gFS	Forward Transconductance	$V_{DS}=5\text{V}, I_D=50\text{A}$		130	--	S
Ciss	Input Capacitance	$V_{GS} = 0\text{V} \quad V_{DS} = 50\text{V} \quad f = 1.0\text{MHz}$	--	4282	--	pF
Coss	Output Capacitance		--	429	--	pF
Crss	Reverse Transfer Capacitance		--	17	--	pF
Rg	Gate resistance		--	2.5	--	Ω
td(ON)	Turn-on Delay Time	$I_D = 20\text{A} \quad V_{DS} = 50\text{V} \quad V_{GS} = 10\text{V} \quad R_G = 5\Omega$	--	20	--	ns
tr	Rise Time		--	11	--	ns
td(OFF)	Turn-Off Delay Time		--	55	--	ns
tf	Fall Time		--	28	--	ns
Qg	Total Gate Charge	$V_{GS} = 0\sim 10\text{V} \quad V_{DS} = 50\text{V} \quad I_D = 20\text{A}$	--	61.4	--	nC
Qgs	Gate Source Charge		--	17.4	--	nC
Qgd	Gate Drain Charge		--	14.1	--	nC
IS	Diode Forward Current	$T_c = 25^\circ\text{C}$	--	--	100	A
ISM	Diode Pulse Current		--	--	320	A
VSD	Diode Forward Voltage	$I_S=6.0\text{A}, V_{GS}=0\text{V}$	--	--	1.2	V
trr	Reverse Recovery time	$I_S=20\text{A}, V_{DD}=50\text{V} \quad dI_F/dt=100\text{A}/\mu\text{s}$	--	100	--	ns
Qrr	Reverse Recovery Charge		--	250	--	nC

Note :

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3、The EAS data shows Max. rating . The test condition is $VDD=50\text{V}$, $L=0.3\text{mH}$, $Rg=25\Omega$, Starting $TJ=25^\circ\text{C}$
- 4、The power dissipation is limited by 150°C junction temperature

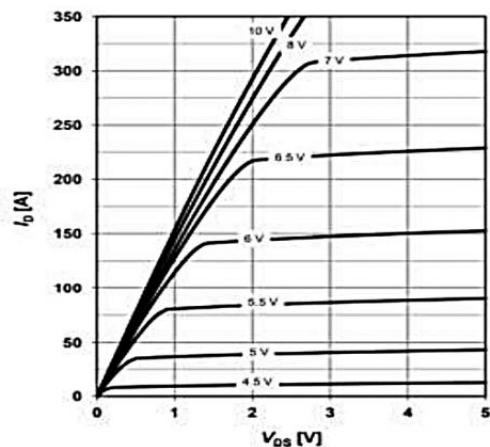
Typical Characteristics

Figure1: output characteristics

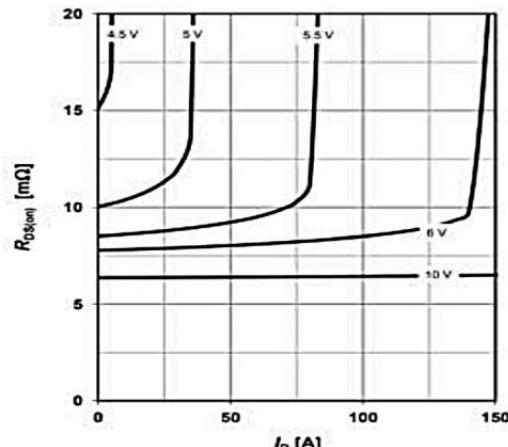


Figure2 Typical drain source on resistance

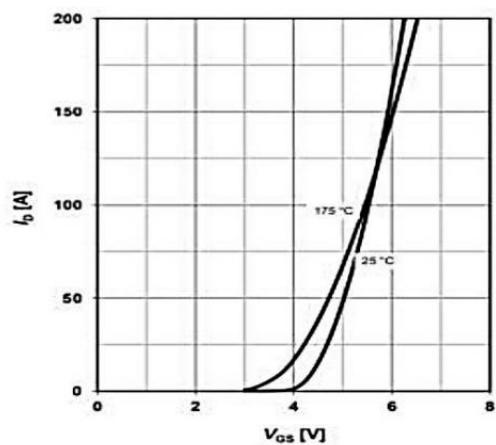


Figure3: transfer characteristics

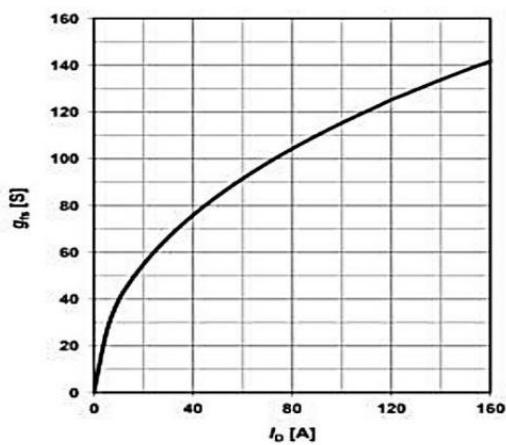


Figure4: forward transconductance

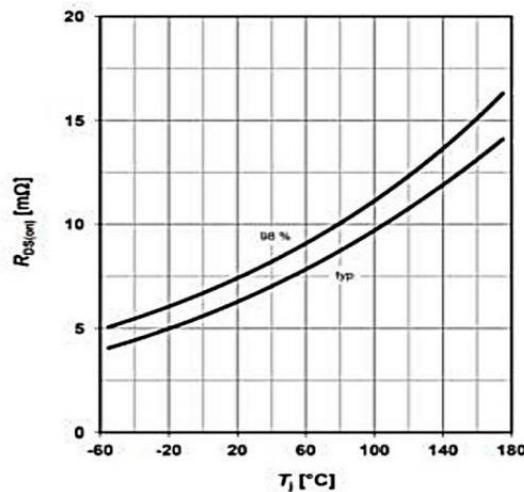


Figure5: Drain-source on-state resistance

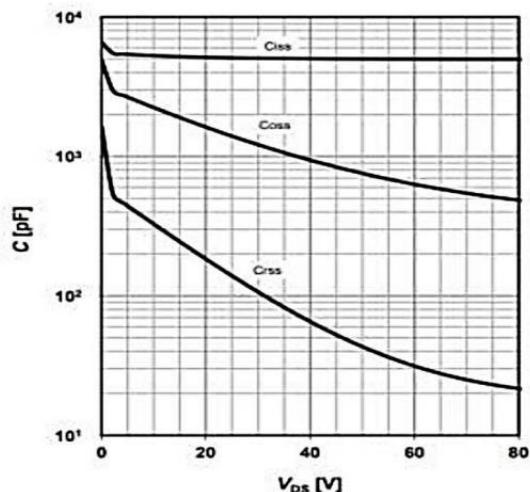


Figure6: Typ. capacitances

Typical Characteristics

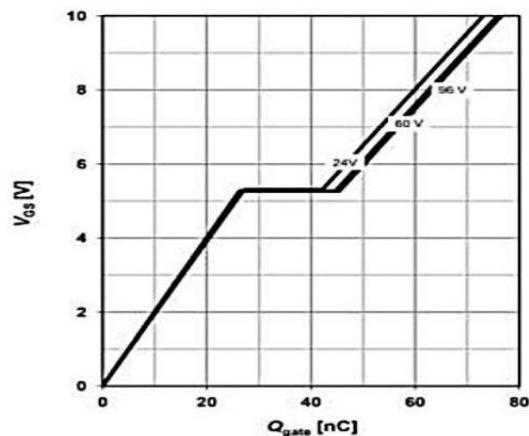


Figure7: Typ. gate charge voltage

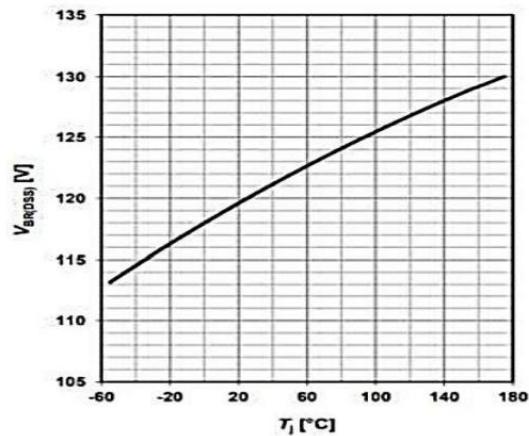


Figure8: Drain-source breakdown

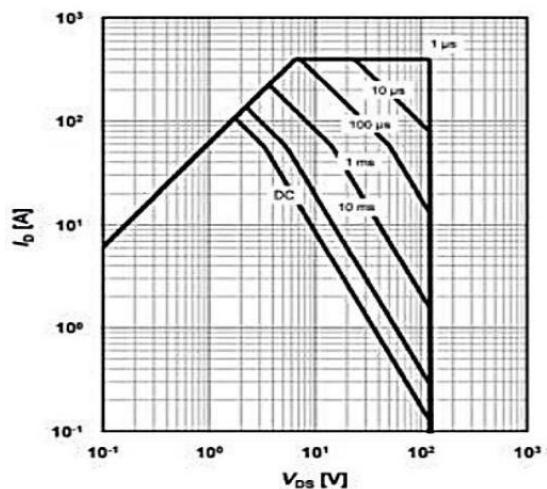


Figure9: Safe operating area

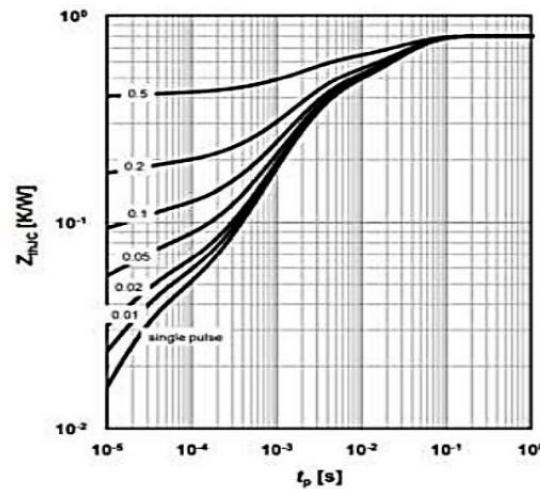
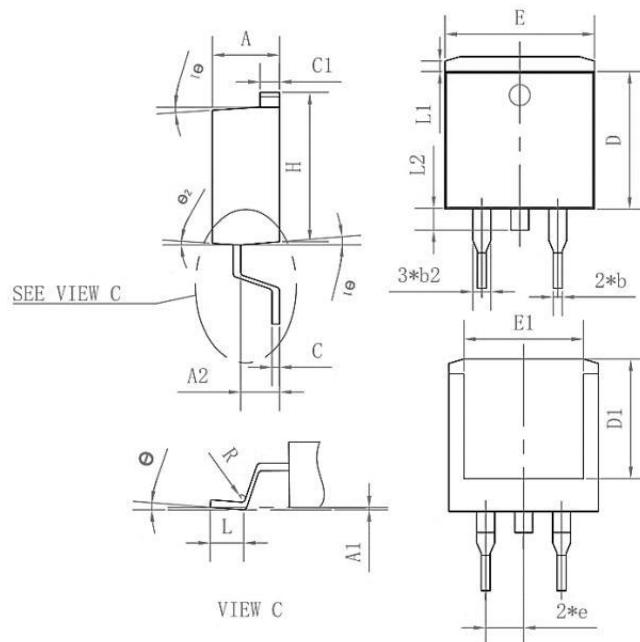


Figure10: Max. transient thermal impedance

Package Mechanical Data-TO-263-3L-SLK



Symbol	Common		
	Mim	mm Nom	Max
A	4.35	4.47	4.60
A1	0.09	0.10	0.11
A2	2.30	2.40	2.70
b	0.70	0.80	1.00
b2	1.25	1.36	1.50
C	0.45	0.50	0.65
C1	1.29	1.30	9.40
D	9.10	9.20	9.30
D1	7.90	8.00	8.10
E	9.85	10.00	10.20
E1	7.90	8.00	8.10
H	15.30	15.50	15.70
e	-	2.54	-
L	2.34	2.54	2.74
L1	1.00	1.10	1.20
L2	1.30	1.40	1.50
R	0.24	0.25	0.26
θ	0°	4°	8°
Θ_1	4°	7°	10°
Θ_2	0°	3°	6°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	TO-263-3L		800